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(54) **LARGE-AREA III-V SEMICONDUCTOR
LAYER TRANSFERRING METHOD**

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ABSTRACT

Disclosed is a large-area III-V semiconductor layer transferring method. The large-area III-V semiconductor layer transferring method includes: forming III-V semiconductor dies on a lower substrate; forming dielectric patterns on the III-V semiconductor dies and the lower substrate exposed between the III-V semiconductor dies; forming a lower III-V semiconductor layer on the dielectric patterns and the III-V semiconductor dies; forming a sacrificial layer on the lower III-V semiconductor layer; forming an upper III-V semiconductor layer on the sacrificial layer; bonding an upper substrate onto the III-V semiconductor layer; and removing the sacrificial layer.

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